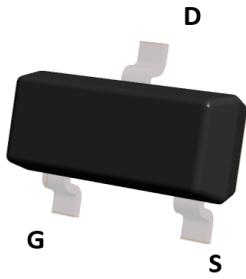
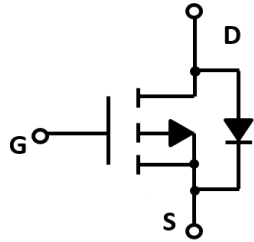
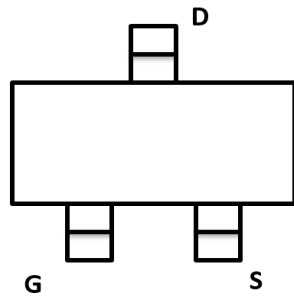


## P-Channel Enhancement Mode Field Effect Transistor



Top View

**SOT-23**



### Product Summary

- $V_{DS}$  -30V
- $I_D$  -3.0A
- $R_{DS(ON)}$ ( at  $V_{GS}=-10V$ ) <85 mohm
- $R_{DS(ON)}$ ( at  $V_{GS}=-4.5V$ ) <105 mohm

### General Description

- Trench Power LV MOSFET technology
- High density cell design for Low  $R_{DS(ON)}$
- High Speed switching

### Applications

- PMW applications
- Load switch
- Power management

### ■ Absolute Maximum Ratings ( $T_A=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Maximum	Unit
Drain-source Voltage	$V_{DS}$	-30	V
Gate-source Voltage	$V_{GS}$	$\pm 20$	V
Drain Current	$I_D$	$T_A=25^\circ\text{C}$ @ Steady State	-3.0
		$T_A=70^\circ\text{C}$ @ Steady State	-2.4
Pulsed Drain Current <sup>A</sup>	$I_{DM}$	-13	A
Total Power Dissipation @ $T_A=25^\circ\text{C}$	$P_D$	1.1	W
Thermal Resistance Junction-to-Ambient @ Steady State <sup>B</sup>	$R_{\theta JA}$	113	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	$^\circ\text{C}$

### ■ Ordering Information (Example)

PREFERRED P/N	PACKING CODE	Marking	MINIMUM PACKAGE(pcs)	INNER BOX QUANTITY(pcs)	OUTER CARTON QUANTITY(pcs)	DELIVERY MODE
YJL2303A	F2	S3A.	3000	30000	120000	7" reel



# YJL2303A

## ■ Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)

Parameter	Symbol	Conditions	Min	Typ	Max	Units
<b>Static Parameter</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±20V, V <sub>DS</sub> =0V			±100	nA
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.0	-1.5	-2.4	V
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -10V, I <sub>D</sub> =-3.0A		60	85	mΩ
		V <sub>GS</sub> = -4.5V, I <sub>D</sub> =-2.0A		80	105	
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-3.0A, V <sub>GS</sub> =0V		-0.8	-1.2	V
Maximum Body-Diode Continuous Current	I <sub>S</sub>				-3.0	A
<b>Dynamic Parameters</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1MHZ		375		pF
Output Capacitance	C <sub>oss</sub>			63		
Reverse Transfer Capacitance	C <sub>rss</sub>			47		
<b>Switching Parameters</b>						
Total Gate Charge	Q <sub>g</sub>	V <sub>GS</sub> =-10V, V <sub>DS</sub> =-15V, I <sub>D</sub> =-3.0		4.2		nC
Gate Source Charge	Q <sub>gs</sub>			1.0		
Gate Drain Charge	Q <sub>gd</sub>			1.3		
Turn-on Delay Time	t <sub>D(on)</sub>	V <sub>GS</sub> =-10V, V <sub>DD</sub> =-15V, R <sub>L</sub> =15Ω, I <sub>D</sub> =-1A, R <sub>GEN</sub> =2.5Ω		14		ns
Turn-on Rise Time	t <sub>r</sub>			61		
Turn-off Delay Time	t <sub>D(off)</sub>			19		
Turn-off Fall Time	t <sub>f</sub>			10		

A. Pulse Test: Pulse Width ≤ 300us, Duty cycle ≤ 2%.

B. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch.

## ■ Typical Performance Characteristics

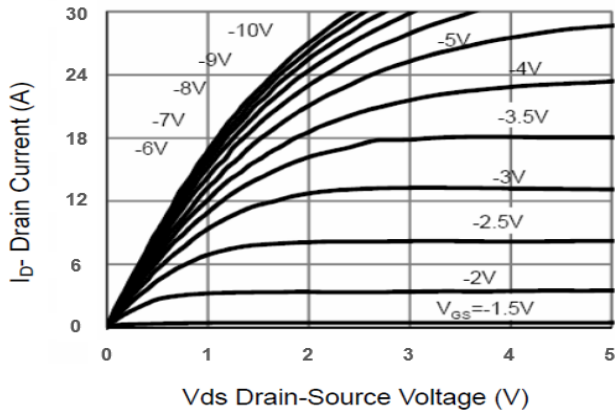


Figure1. Output Characteristics

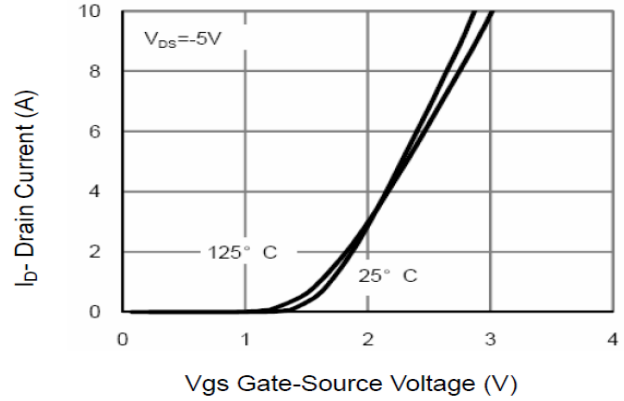


Figure2. Transfer Characteristics

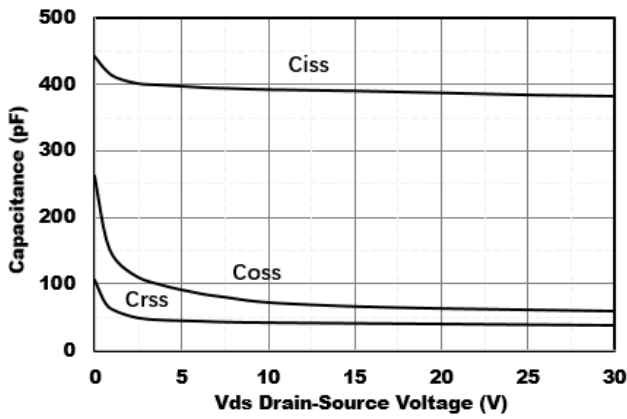


Figure3. Capacitance Characteristics

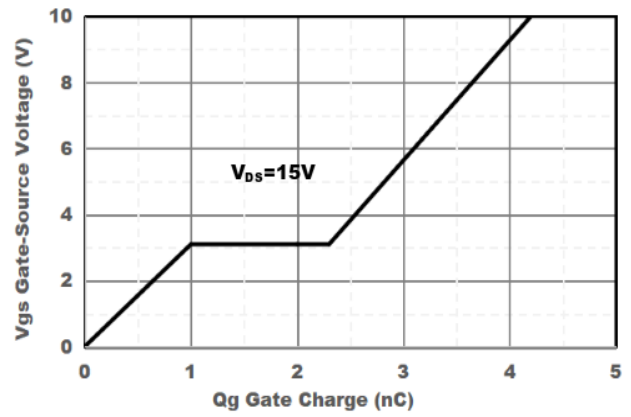


Figure4. Gate Charge

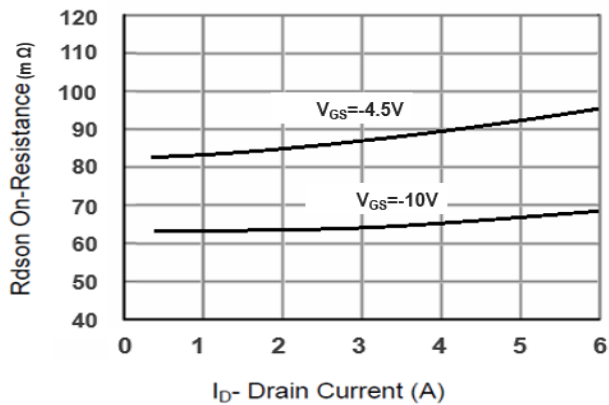


Figure5. Drain-Source on Resistance

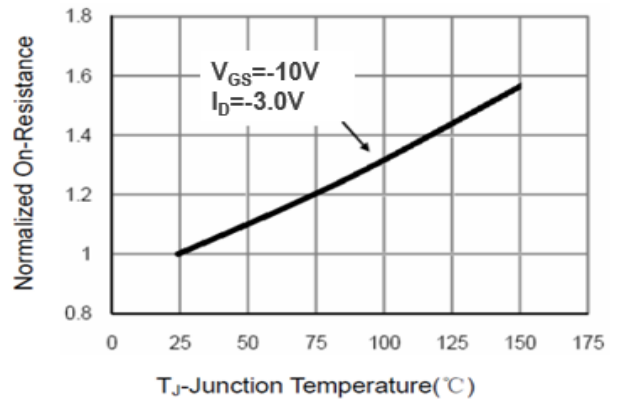


Figure6. Drain-Source on Resistance



# YJL2303A

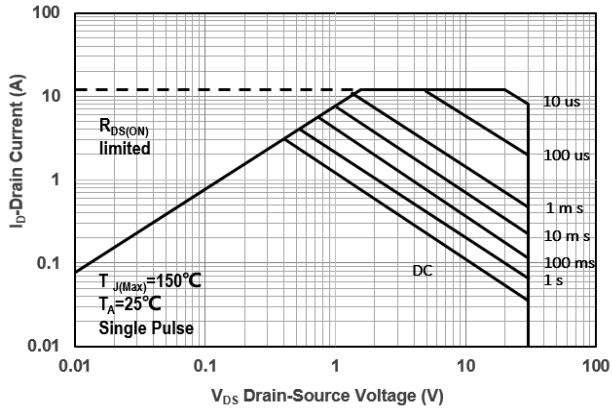


Figure7. Safe Operation Area

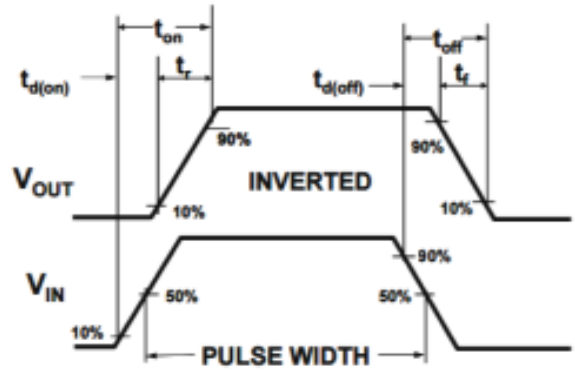
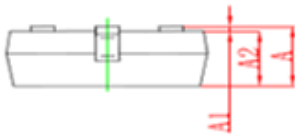
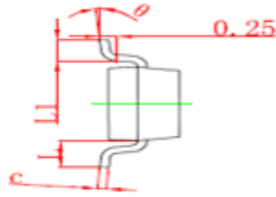
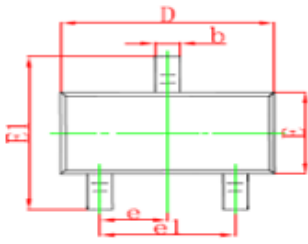


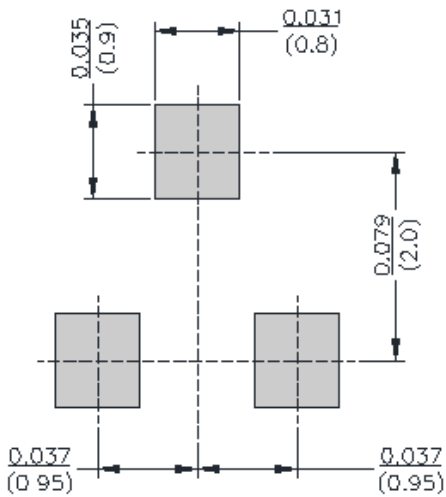
Figure8. Switching wave

## ■ SOT-23 Package information



Symbol	Dimensions in Millimeter		Dimensions in Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950Type		0.037Type	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.220REF	
L1	0.300	0.500	0.012	0.020
$\theta$	0°	8°	0°	8°

## ■ SOT-23 Suggested Pad Layout





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